FIG. 1

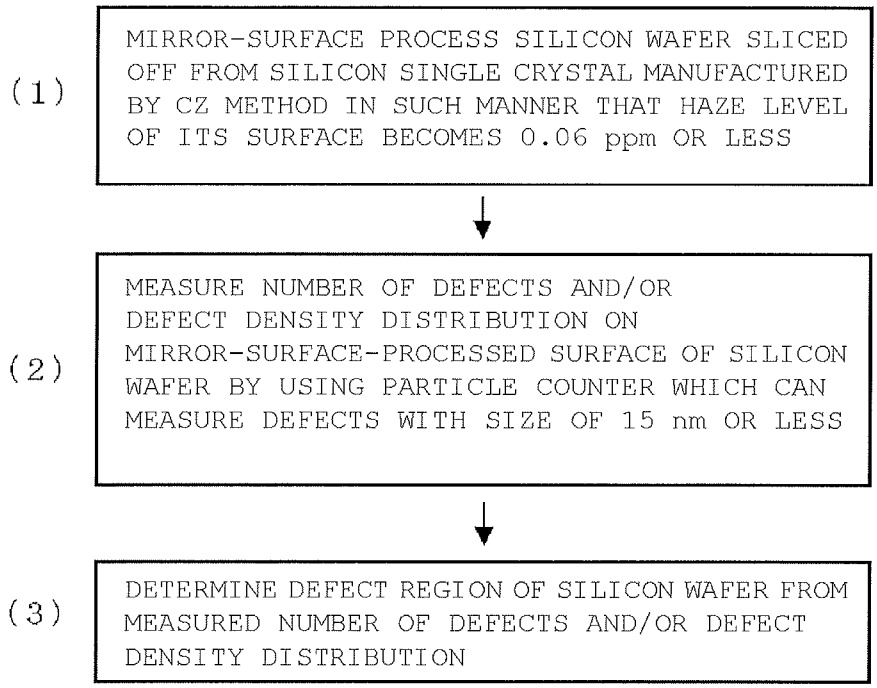
(1)
MIRROR-SURFACE PROCESS SILICON WAFER SLICED OFF FROM SILICON SINGLE CRYSTAL MANUFACTURED BY CZ METHOD IN SUCH MANNER THAT HAZE LEVEL OF ITS SURFACE BECOMES 0.06 ppm OR LESS
(2)
MEASURE NUMBER OF DEFECTS AND/OR DEFECT DENSITY DISTRIBUTION ON MIRROR-SURFACE-PROCESSED SURFACE OF SILICON WAFER BY USING PARTICLE COUNTER WHICH CAN MEASURE DEFECTS WITH SIZE OF 15 nm OR LESS
(3)
DETERMINE DEFECT REGION OF SILICON WAFER FROM MEASURED NUMBER OF DEFECTS AND/OR DEFECT DENSITY DISTRIBUTION

FIG. 2

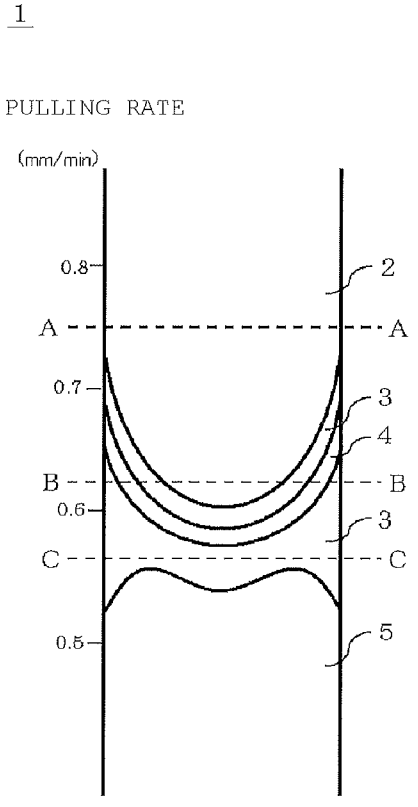
1
PULLING RATE
(mm/min)
0.8
A
0.7
B
0.6
C
0.5
2
3
4
3
5

FIG. 3

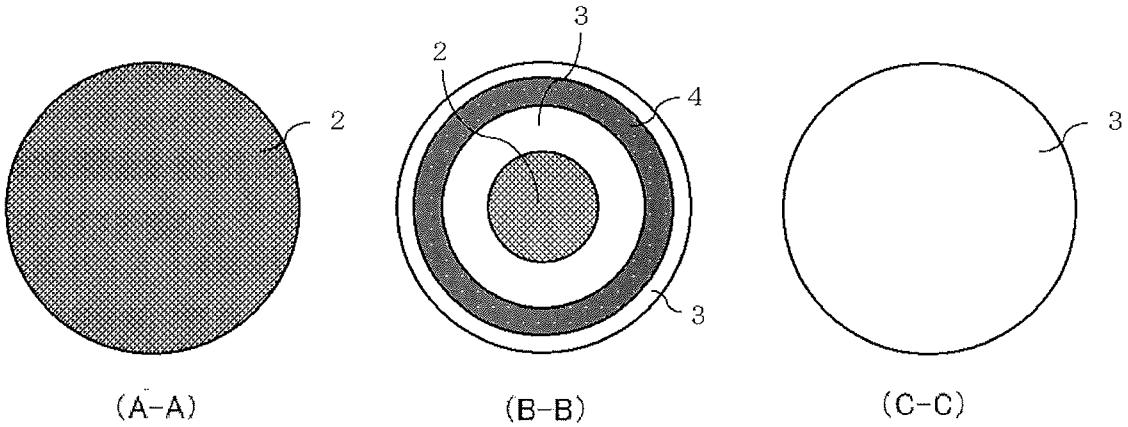

FIG. 4

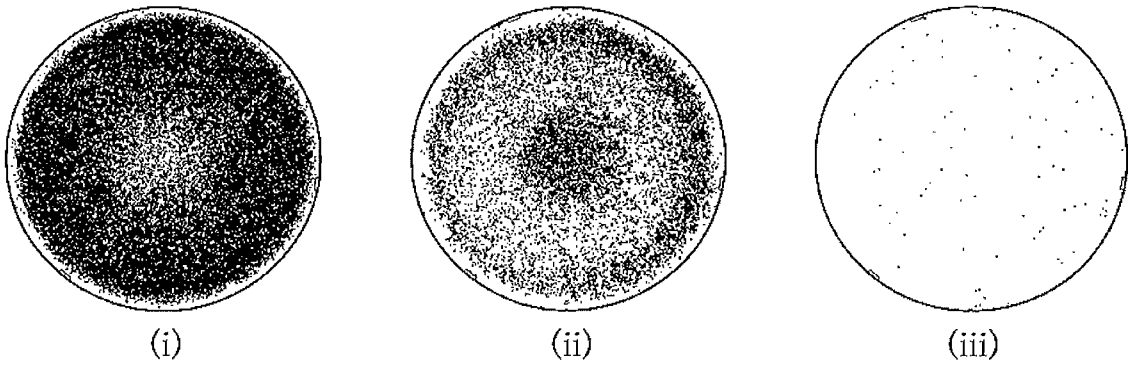

FIG. 5

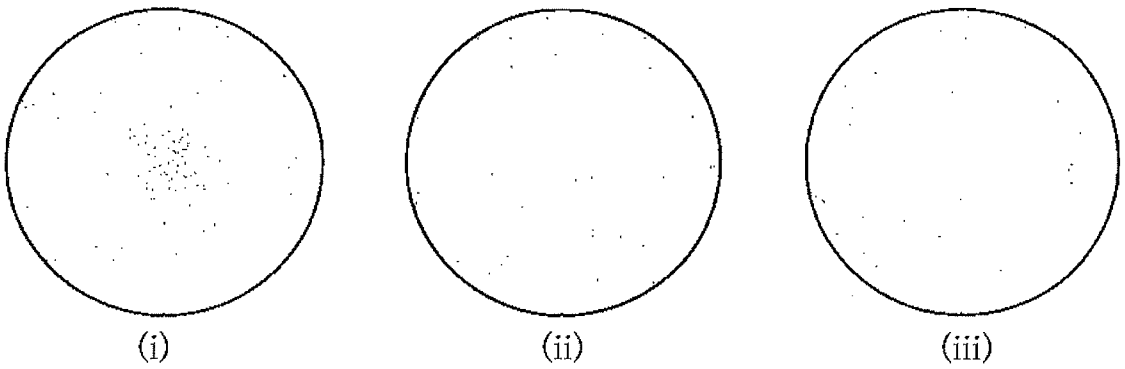
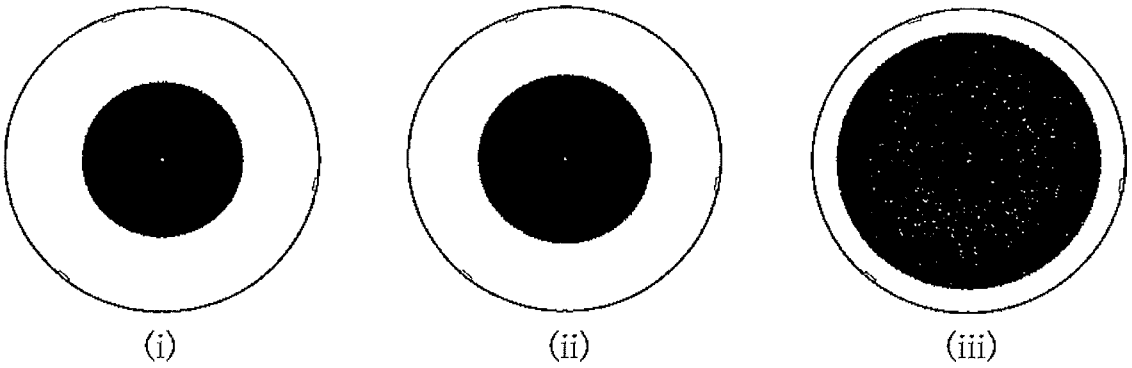
FIG. 6